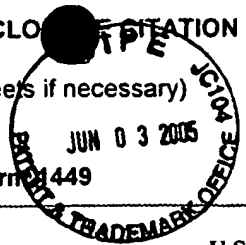


<b>INFORMATION DISCLOSURE CITATION</b>  (Use several sheets if necessary) <b>PTO Form 1449</b>				Attorney Docket No. 040894-7183		Application No.: 10/525,045	
				Applicants: Shigeki SAKAI		PAGE 1 of 1	
				Filing Date: February 18, 2005		Group Art Unit: Unassigned	
<b>U.S. PATENT DOCUMENTS</b>							
*Examiner Initial		Document Number	Date	Name	Class	Sub Class	Filing Date
MDH		6,060,755	May 9, 2000	Ma et al.	-	-	
↓		2003/0027360 A1	Feb. 6, 2003	Hsu et al.	-	-	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Sub Class	<u>Translation</u> YES NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
MDH		Hag-Ju CHO, et al., "Structural and Electrical Properties of HfO <sub>2</sub> With Top Nitrogen Incorporated Layer", <i>IEEE Electron Device Letters</i> , Vol. 23, No. 5, May 2002, pages 249-251.					
↓		Hoon Sang CHOI, et al., "Electrical Characteristics of Pt/SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>7</sub> /Si Using Ta <sub>2</sub> O <sub>5</sub> as the Buffer Layer", <i>2001 The Japan Society of Applied Physics</i> , Jpn. J. Appl. Phys. Vol. 40 (2001), Part 1, No. 4B, April 2001, pages 2940-2942					
↓		Kyu-Jeong CHOI, et al., "Metal/ferroelectric/insulator/semiconductor structure of Pt/Sr Bi <sub>2</sub> Ta <sub>2</sub> O <sub>7</sub> /YMnO <sub>3</sub> /Si using YMnO <sub>3</sub> as the buffer layer", <i>1999 American Institute of Physics</i> , Applied Physics Letters, Vol. 75, No. 5, August 2, 1999, pages 722-724.					
↓		C. H. CHOI, et al., "Thermally Stable CVD HfO <sub>x</sub> N <sub>y</sub> Advanced Gate Dielectrics with Poly-Si Gate Electrode", <i>2002 IEEE, IEDM</i> , pages 857-860.					
Examiner <i>Monica D. Han</i>				Date Considered <i>8/31/06</i>			
Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

**INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

PTO Form 1449



Attorney Docket No.  
040894-7183

Application No.:  
10/525,0452

Applicant(s): Shigeki SAKAI

PAGE 1 of 1

Filing Date: February 18, 2005

Group Art Unit: 5664

**U.S. PATENT DOCUMENTS**

*Examiner Initial	Document Number	Date	Name	Class	Sub Class	Filing Date

**FOREIGN PATENT DOCUMENTS**

Document Number	Date	Country	Class	Sub Class	Translation YES NO	
JP-A-2001-291841	Oct. 19, 2001	JAPAN			abstract	
JP-A-2002-353420	Dec. 6, 2002	JAPAN			abstract	

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

MDA	S. Migita et al., "Epitaxial Structure $\text{SrBi}_2\text{Ta}_2\text{O}_9<116>/\text{SrTiO}_3<011>/\text{Ce}_{0.12}\text{Zr}_{0.88}<001>/\text{Si}<001>$ for Ferroelectric-Gate FET Memory," <i>Integrated Ferroelectrics</i> , Vol. 40, pp. 2135-143 (2001).
↓	Shinji Migita et al., "Fabrication and Electrical Properties of Ferroelectric-gate FET with Epitaxial Gate Structure," <i>Denshi Jōhō Tūshin Gakkai Ronbun-shi</i> , Vol. J85-C, No. 1 (January 2002 issue), pp. 14-22.

Examiner

*Imperical D. Harrison*

Date Considered

*8/31/06*

Examiner:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.